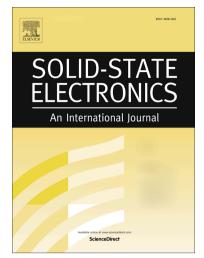
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M.X. Cai, R.H. Yao

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M.X. Cai, R.H. Yao*

Acctin School of Electronic and Information Engineering, South China University of Technology, Guangzhou 510641, PR China

* Corresponding author.

E-mail address: phrhyao@scut.edu.cn (R.H. Yao).

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